

ABSTRACT OF THE DISCLOSURE

A method of producing a silicon carbide single crystal has
storing a sublimation law material on a first end portion
5 in a reaction container;
 disposing a seed crystal of a silicon carbide single crystal
 on a second end portion substantially facing the sublimation
 law material in the reaction container; and
 re-crystallizing the sublimated sublimation law material
10 on the seed crystal to grow a silicon carbide single crystal,
 wherein a sealing portion is provided in the reaction
 container to grow a silicon carbide single crystal on the seed
 crystal provided in the sealing portion while preventing the
 leak of the sublimated sublimation law material from the
15 atmosphere for sublimation.